

OPA5615N

Yellow Green LED Chip

N Side-Up

GaP/GaP

1. Material Substrate GaP (P Type)
Epitaxial Layer GaP (N/P Type)

2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

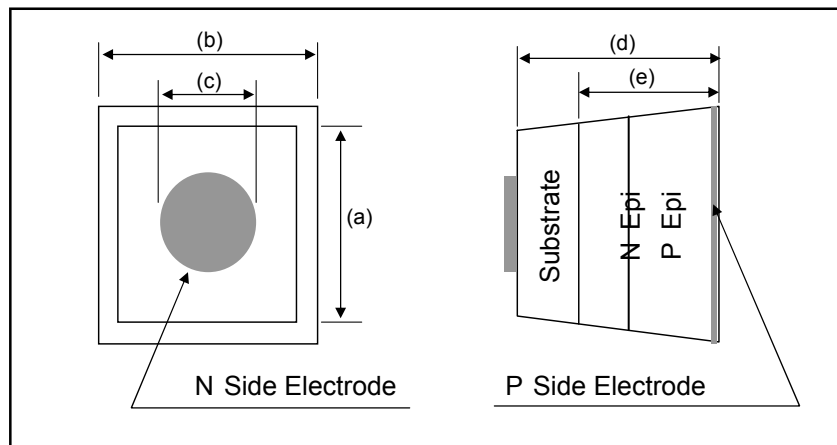
3. Electro-Optical Characteristics

| Parameter | Symbol | Min | Typ | Max | Unit | Condition |
|-----------------|-----------------|-----|-----|-----|------|-----------|
| Forward Voltage | $V_{F(1)}$ | | 1.8 | | V | IF=1mA |
| | $V_{F(2)}$ | | 2.2 | 2.4 | V | IF=20mA |
| Reverse Voltage | V_R | 8 | | | V | IR=10uA |
| Brightness | Iv | 250 | 350 | | mcd | IF=20mA |
| Wavelength | λ_d | | 572 | | nm | IF=20mA |
| | $\Delta\lambda$ | | 30 | | nm | IF=20mA |

※ Note : Brightness is measured by Sorter E/T system with bare chip.

4. Mechanical Data

| | | |
|---------------------|-------|---------------|
| (a) Emission Area | ----- | 13mil x 13mil |
| (b) Bottom Area | ----- | 14mil x 14mil |
| (c) Bonding Pad | ----- | 160um |
| (d) Chip Thickness | ----- | 11mil |
| (e) Junction Height | ----- | 6.8mil |



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